



PATENT ABSTRACTS OF JAPAN

(11) Publication number: **06338591 A**(43) Date of publication of application: **06.12.94**(51) Int. Cl. **H01L 27/092**(21) Application number: **06130826**(22) Date of filing: **23.05.94**(30) Priority: **22.05.93 KR 93 9308878**(71) Applicant: **HYUNDAI ELECTRON IND CO LTD**(72) Inventor: **CHONG IN-SUL
JEONG JAE GOAN**(54) **MANUFACTURE OF COMPLEMENTARY MOS
TRANSISTOR (CMOS)**

COPYRIGHT: (C)1994,JPO

(57) Abstract:

PURPOSE: To obtain a CMOS having enhanced characteristics by a simple process with a method, wherein high-concentration source and drain ion-implanted regions are respectively formed in an N-type well and a P-type well to heat-treat the source and drain ion-implanted regions.

CONSTITUTION: An N-type well 2 and a P-type well 3 are formed in a P-type silicon substrate 1 and thereafter, element isolation oxide films 4 are formed to form an operating region and an insulatingly isolated region. Subsequently, after buffer oxide films 5 are formed on the entire surface of the substrate 1, P-type impurity ions for controlling a threshold voltage are implanted in the entire surface of the substrate 1, including the operating region to form ion-implanted regions 6, and the regions 6 are heat-treated. Thereby, a low-concentration drain region of an N-channel MOSFET and pockets of a P-channel MOSFET can be formed without a masking process.

